

The 22nd International Symposium on Power Semiconductor Devices and ICs



ISPSD'10



2nd Call for Paper

<http://www.ispsd2010.com>

June 6-10, 2010

International Conference Center Hiroshima, JAPAN

Sponsor: The Institute of Electrical Engineers of Japan

Co-Sponsor: IEEE Electron Devices Society

ISPSD is the premier forum for technical discussion in all areas of power semiconductor devices, power integrated circuits, their hybrid technologies, processes, CAD/simulation and applications. Main categories of interest include:

- ◆ High Voltage Power Devices: Medium and high voltage Si bipolar devices such as IGBT, thyristor, pn diode, etc
- ◆ Low Voltage Power Devices: Low and medium voltage Si unipolar devices such as power MOSFETs, SJ type devices, etc
- ◆ New Material Power Devices: Power devices based on compound or new materials such as SiC, GaN, diamond
- ◆ Power ICs: Integrated power devices and circuitry on a single chip architecture
- ◆ Module and Package Technologies: Integrated power modules and packaging technologies (functionality, power density, isolation, reliability, device cooling, temperature endurance, manufacturing, etc)

Deadline for submission of the abstract: October 30, 2009

Paper Submission

- Prospective authors should visit the ISPSD'10 website: <http://www.ispsd2010.com>
- A PDF formatted abstract should be submitted through this website including:
 - A one page text summary in English (500 words maximum)
 - Up to two pages of supporting figures
 - The abstract heading must include: Title, Authors, Affiliations, Address, Phone, Fax, E-mail
 - Abstracts Must Clearly State: Purpose of work; How the work is differentiated from prior work; Specific results and their significance; Up-to-date references
- Notice of acceptance will be sent to the authors by January, 2010.
- The final manuscript, in English, will be required no later than March, 2010.
- If the first author as a presenter of a paper is no more than 30 years at the time of the conference, their work will be considered for the Charitat Award.
The abstract must be identified at the time of submission.

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